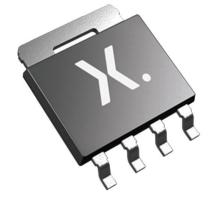


PSMN8R0-80YLX Datasheet

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DiGi Electronics Part Number	PSMN8R0-80YLX-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PSMN8R0-80YLX
Description	MOSFET N-CH 80V 100
Detailed Description	N-Channel 80 V 100A

OSFET N-CH 80V 100A LFPAK56

-Channel 80 V 100A (Ta) 238W (Ta) Surface Moun t LFPAK56, Power-SO8

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PSMN8R0-80YLX	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
80 V	100A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
5V, 10V	8m0hm @ 25A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.1V @ 1mA	104 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	8167 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	238W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
LFPAK56, Power-SO8	SC-100, SOT-669
Base Product Number:	
PSMN8R0	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



PSMN8R0-80YL

N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56 20 October 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

2. Features and benefits

- Advanced TrenchMOS provides low R_{DSon} and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

. . . .

- Synchronous rectification in power supply equipment
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

. . .

1.11

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	80	V
ID	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	238	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	6.3	8.5	mΩ
Dynamic cl	naracteristics			1			
Q _{GD}	gate-drain charge	$I_{D} = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	17.1	-	nC

[1] Continuous current is limited by package.

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PSMN8R0-80YL

N-channel 80 V, 8 m logic level MOSFET in LFPAK56

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G LIFE
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN8R0-80YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	238	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	А
	V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	75	А	
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	423	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	423	А

PSMN8R0-80YL

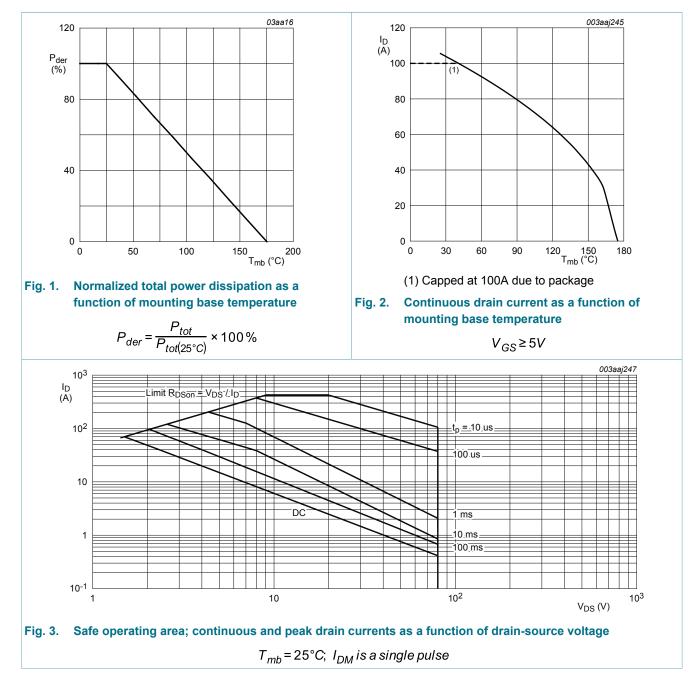
N-channel 80 V, 8 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Мах	Unit
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2][3]	-	148	mJ

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

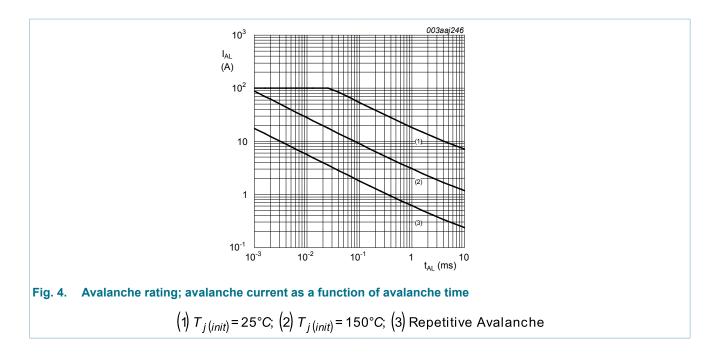
[3] Refer to application note AN10273 for further information.



Product data sheet

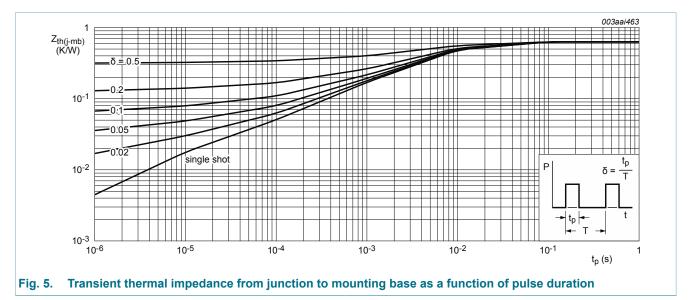
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N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56



8. Thermal characteristics

Table 5. T	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.63	K/W



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N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56

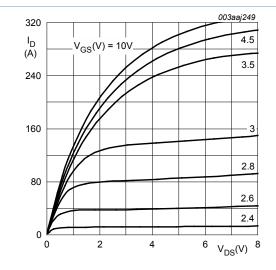
9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					_
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	80	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	72	-	-	V
V _{GS(th)} gate-source thresho voltage	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9;</u> <u>Fig. 10</u>	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.07	10	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	6.3	8.5	mΩ
resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	5.8	8	mΩ	
	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	21.3	mΩ	
Dynamic c	naracteristics					
Q _{G(tot)}	total gate charge	$I_{D} = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	104	-	nC
		I _D = 25 A; V _{DS} = 64 V; V _{GS} = 5 V;	-	54.7	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	13.5	-	nC
Q _{GD}	gate-drain charge	-	-	17.1	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	6125	8167	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	397	476	pF
C _{rss}	reverse transfer capacitance		-	207	284	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 5 V;	-	28	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	50	-	ns
t _{d(off)}	turn-off delay time		-	82	-	ns
t _f	fall time		-	45	-	ns
Source-dra	in diode		I	1		
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V

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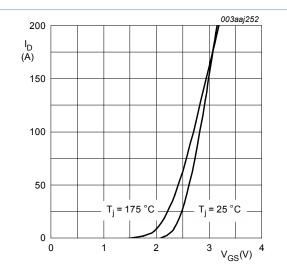
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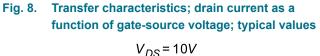
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;	-	30.9	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	36.3	-	nC



T_j = 25 °C; t_p = 300 μs







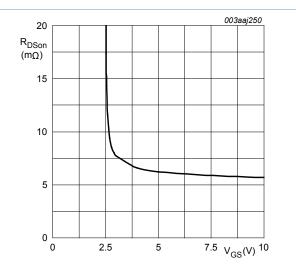


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_i = 25^{\circ}C; I_D = 25A$

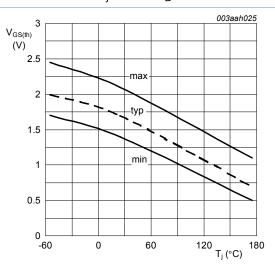
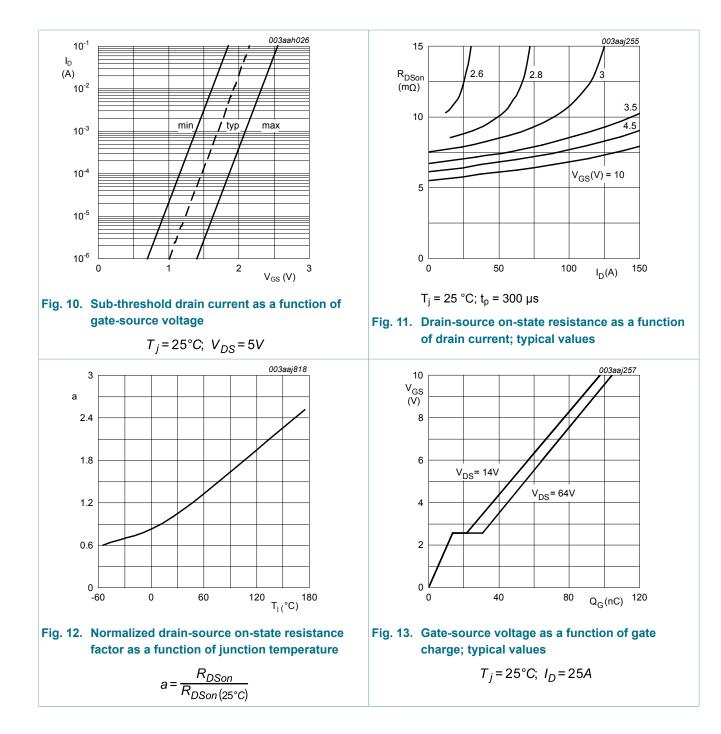


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

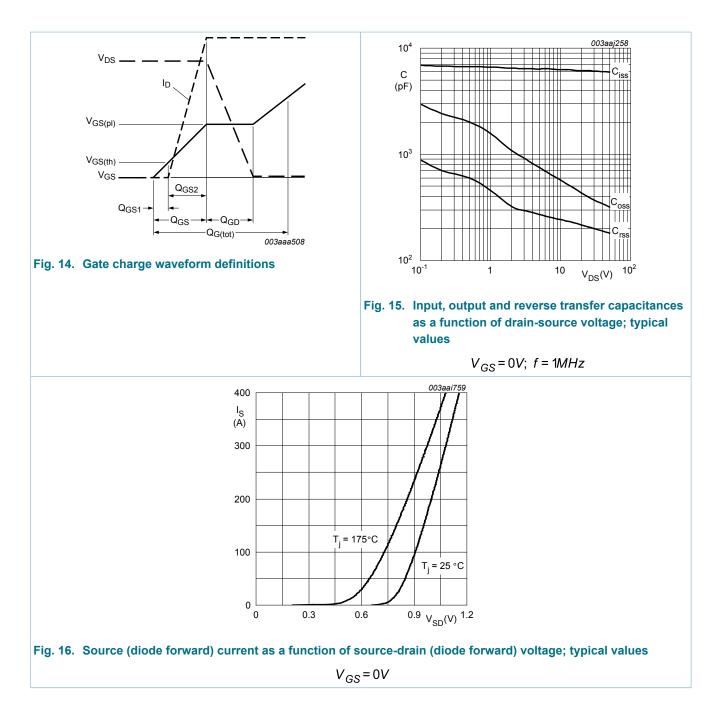
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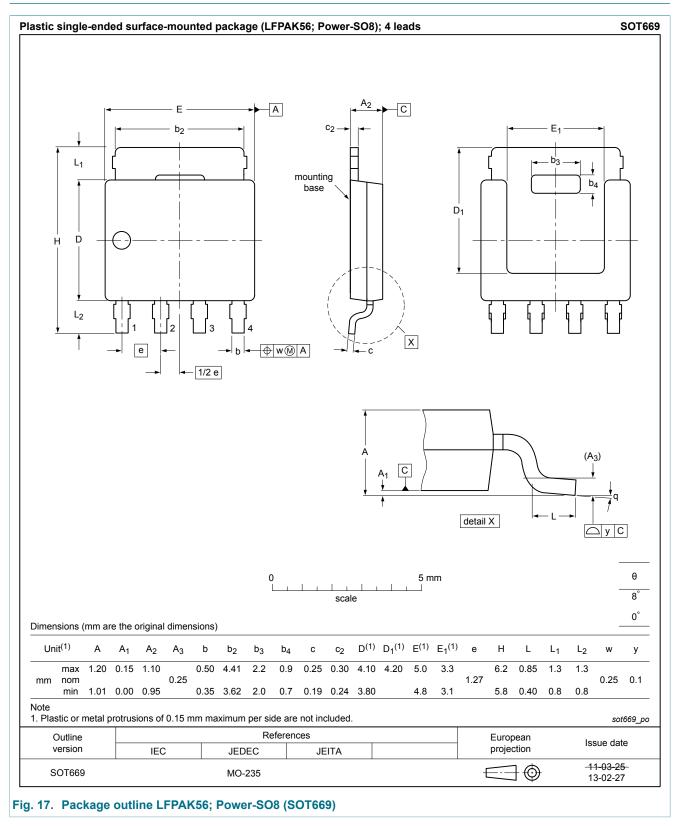
N-channel 80 V, 8 m logic level MOSFET in LFPAK56



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10. Package outline



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N-channel 80 V, 8 mΩ logic level MOSFET in LFPAK56

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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